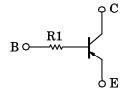
TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

RN2970, RN2971

SWITCHING, INVERTER CIRCUIT, INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATIONS.

- Including Two Devices in US6 (Ultra Super Mini Type with 6 leads)
- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process
- Complementary to RN1970~RN1971

EQUIVALENT CIRCUIT



MAXIMUM RATINGS ($Ta = 25^{\circ}C$) (Q1, Q2 COMMON)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-50	V
Collector-Emitter Voltage	v_{CEO}	-50	V
Emitter-Base Voltage	$ m v_{EBO}$	-5	V
Collector Current	$I_{\mathbb{C}}$	-100	mA
Collector Power Dissipation	PC*	200	mW
Junction Temperature	$T_{ m j}$	150	°C
Storage Temperature Range	$ m T_{stg}$	-55~150	°C

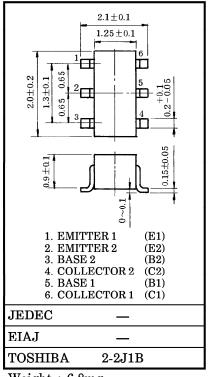
* : Total Rating

FLECTRICAL CHARACTERISTICS (Ta = 25°C) (O1 O2 COMMON)

ELECTRICAL CHARACTERISTICS (Ta = 25°C) (Q1, Q2 COMMON)							
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -50V, I_{E} = 0$	_		-100	nA
Emitter Cut-off Current		$I_{ m EBO}$	$V_{EB} = -5V, I_C = 0$		_	-100	nA
DC Current Gain		${ m h_{FE}}$	$V_{CE} = -5V$, $I_C = -1mA$	120	_	400	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	$I_{C} = -5 \text{mA}, I_{B} = -0.25 \text{mA}$	_	-0.1	-0.3	V
Transition Frequency		${f f}_{ m T}$	$V_{CE} = -10V, I_{C} = -5mA$	_	200		MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = -10V, I_{E} = 0, f = 1MHz$	_	3	6	рF
Input Resistor	RN2970	R1	_	3.29	4.7	6.11	kΩ
	RN2971			7	10	13	

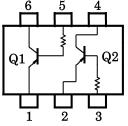
961001EAA2

Unit in mm



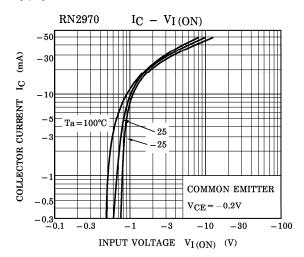
Weight: 6.8mg

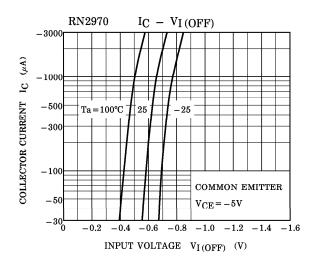
EQUIVALENT CIRCUIT (TOP VIEW)

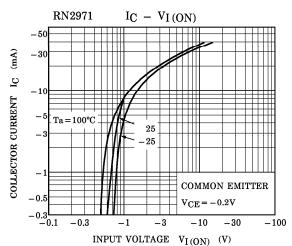


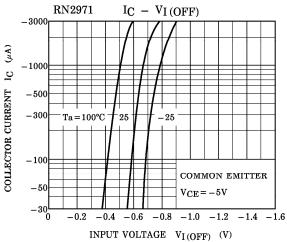
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(Q1, Q2 COMMON)





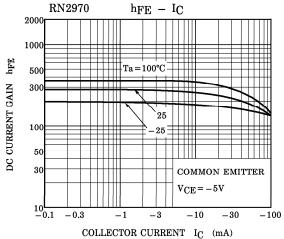


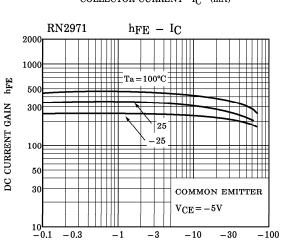


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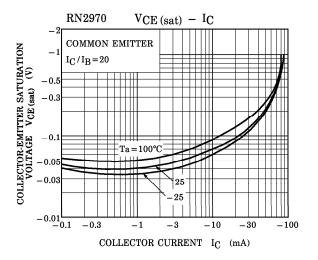
The information contained herein is subject to change without notice.

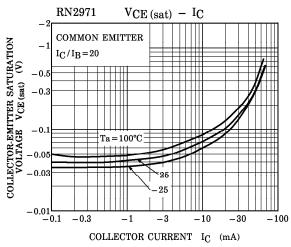
(Q1, Q2, COMMON)





COLLECTOR CURRENT IC (mA)





TYPE NAME	MARKING	
RN2970	Type Name YY K	
RN2971	Type Name YY M	